

1 **Supplementary information for: Optically addressable**
2 **spin defects coupled to bound states in the continuum**
3 **metasurfaces**

4 L. Sortino et al.

5 **Supplementary Note 1: hBN metasurfaces Q factors**

6 **Supplementary Note 2: Transmission of hBN qBIC metasurfaces**

7 **Supplementary Note 3: PL enhancement of coupled spin defects**

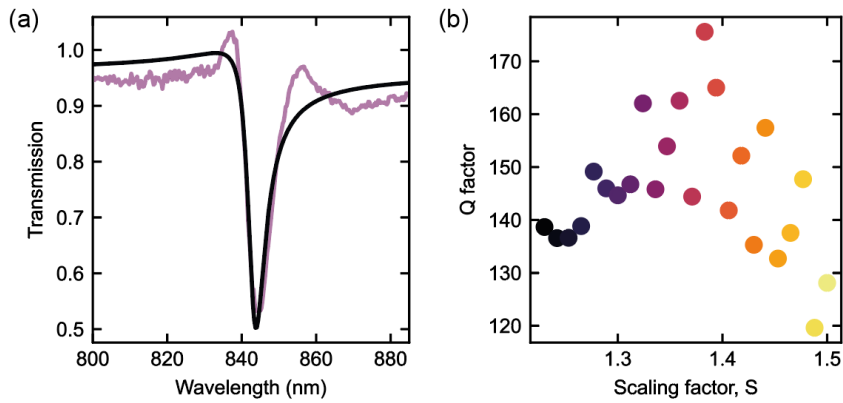
8 **Supplementary Note 4: ODMR Signal-to-Noise ratio analysis**

9 **Supplementary Note 5: qBIC electric field numerical simulations**

10 **Supplementary Note 6: Radiation patterns of in-plane and out-of-plane**
11 **dipoles coupled with hBN metasurfaces.**

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13 **Supplementary Note 1: hBN metasurfaces Q factors**



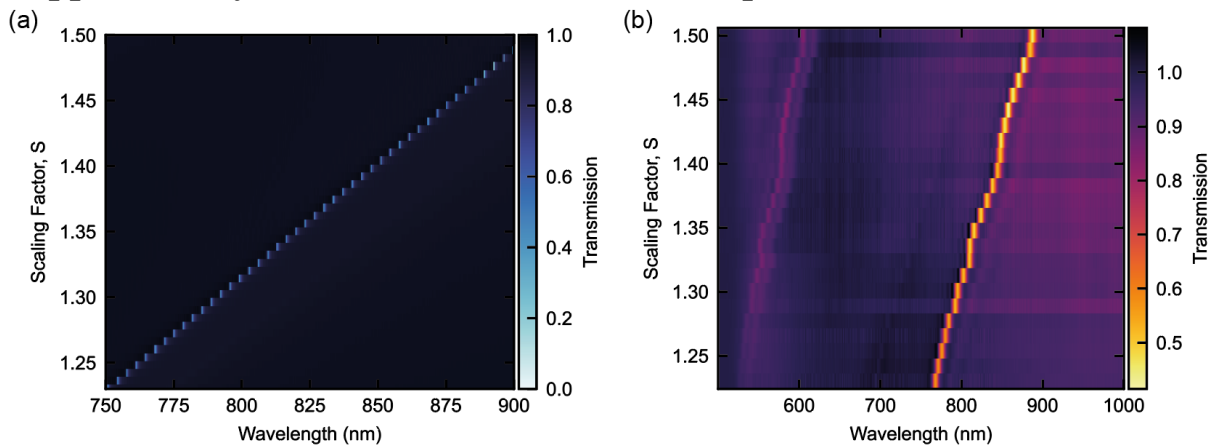
14 Supplementary Figure 1: (a) Transmission spectrum (in purple) of a fabricated hBN metasurface fitted
15 with a Fano function (in black). (b) Extracted Q factors values for metasurfaces with different scaling
16 factors.

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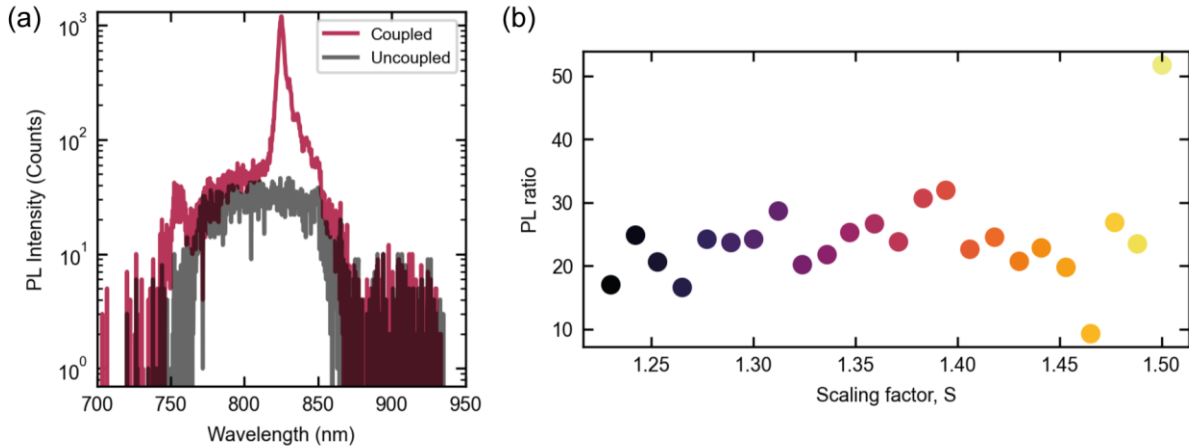
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20 **Supplementary Note 2: Transmission of hBN qBIC metasurfaces**



21 Supplementary Figure 2: (a) Numerically FDTD calculated transmission spectra of hBN qBIC
22 metasurfaces on glass substrate with ($\Delta L = 50$ nm). (b) Transmission spectra of the fabricated hBN
23 metasurfaces under parallel excitation. We observe the appearance of a second peak at higher
24 wavelength. The fabricated samples exhibit a smaller Q factor than numerical simulations, owing to
25 defects and imperfections introduced during the fabrication and ion irradiation processes.

26 **Supplementary Note 3: PL enhancement of coupled spin defects**

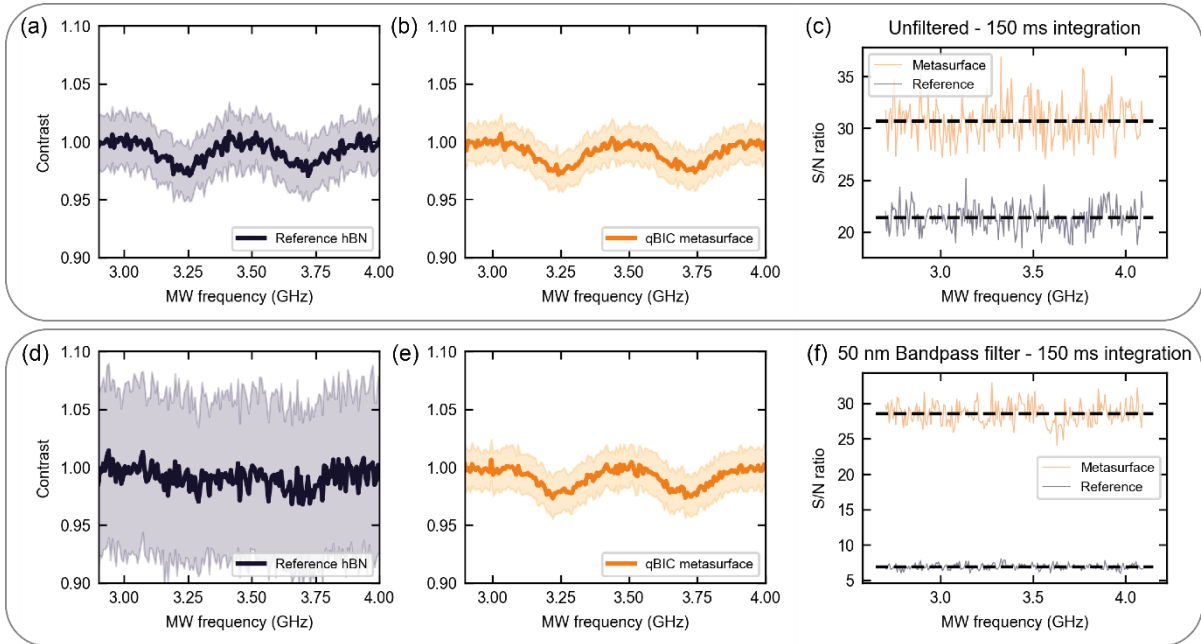


27 Supplementary Figure 3: (a) Raw PL emission spectra from V_B^- defects coupled to a qBIC metasurface
 28 (red) and on the unpatterned reference area (gray). (b) PL enhancement for defects coupled to hBN
 29 metasurfaces. The PL enhancement (I/I_0) is defined as the ratio between the integrated PL intensity of
 30 coupled defects (I) and the reference hBN PL emission (I_0), extracted from the data shown in Figure 3d
 31 in the main text.

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33 **Supplementary Note 4: ODMR Signal-to-Noise ratio analysis**

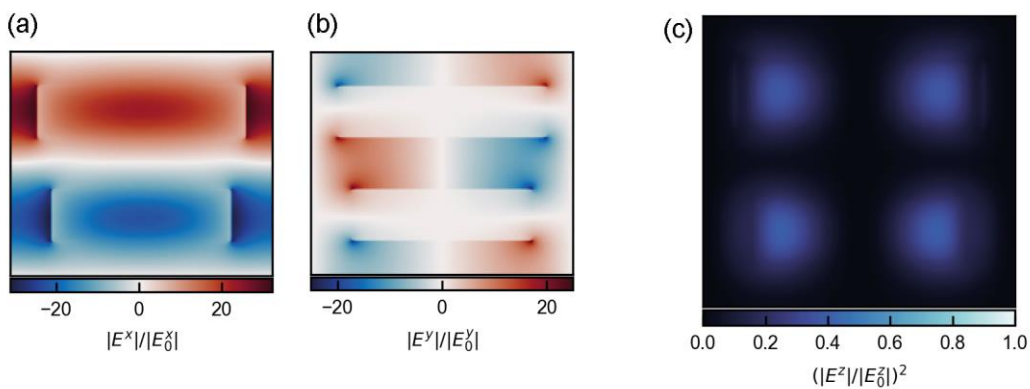
34 The ODMR contrast for the unpatterned hBN reference sample is shown in Figure S4a, the data is
 35 integrated over 150 cycles with 1 ms integration time for each MW frequency. To compare with the
 36 patterned metasurface (Figure S4b), we define the Signal-to-Noise ratio ($S/N = P_{avg}/P_{std}$) as the ratio
 37 between the average value of the PL intensity (P_{avg} , solid line in Figure S4a,b) and the standard deviation
 38 of the PL signal at each MW frequency (P_{std}). We show the extracted value of this S/N ratio in Figure
 39 S4c. For unfiltered collection, we observe a small increase in the S/N ratio for the hBN metasurfaces
 40 from 21.3 to a value of 30.6. However, when inserting the 50 nm bandpass filter, we do not resolve a
 41 clear ODMR contrast anymore for the unstructured sample (Figure S4d). In contrast, the narrow
 42 emission from the metasurfaces funnels the light into the filter bandwidth and shows a clear ODMR
 43 contrast (Figure S4e). In Figure S4f, we plot the S/N ratio for the filtered collection and with 150 ms
 44 integration time, showing a large increase compared to the unfiltered case. The S/N is enhanced from
 45 approximately 1.42 times in the unfiltered case, up to 4.13 in case of bandpass filter, as shown in Figures
 46 S4c,f, where we plot the S/N ratio for whole MW range investigated. The dashed black line represents
 47 the average S/N value.



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 50 Supplementary Figure 4: (a-b) Unfiltered ODMR signal from the unstructured hBN reference sample
 51 (a) and a qBIC hBN metasurface (b). (c) Signal-to-Noise (S/N) ratio for unfiltered PL collection for the
 52 qBIC metasurface (orange) and unstructured sample (grey), averaged over 150 ms integration for each
 53 MW frequency. The dashed black line represents the average value. (d-e) Reproduction of Figure 3f-g
 54 from the main text of the manuscript: ODMR signal after a 775 ± 25 nm bandpass filter is placed in the
 55 collection path, from the unstructured hBN reference sample (d) and a qBIC hBN metasurface (e),
 56 integrated over 150 ms for each MW frequency. (f) Signal-to-Noise ratio for Figures S4d-e. The dashed
 57 black line represents the average value.

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59 Supplementary Note 5: qBIC electric field numerical simulations

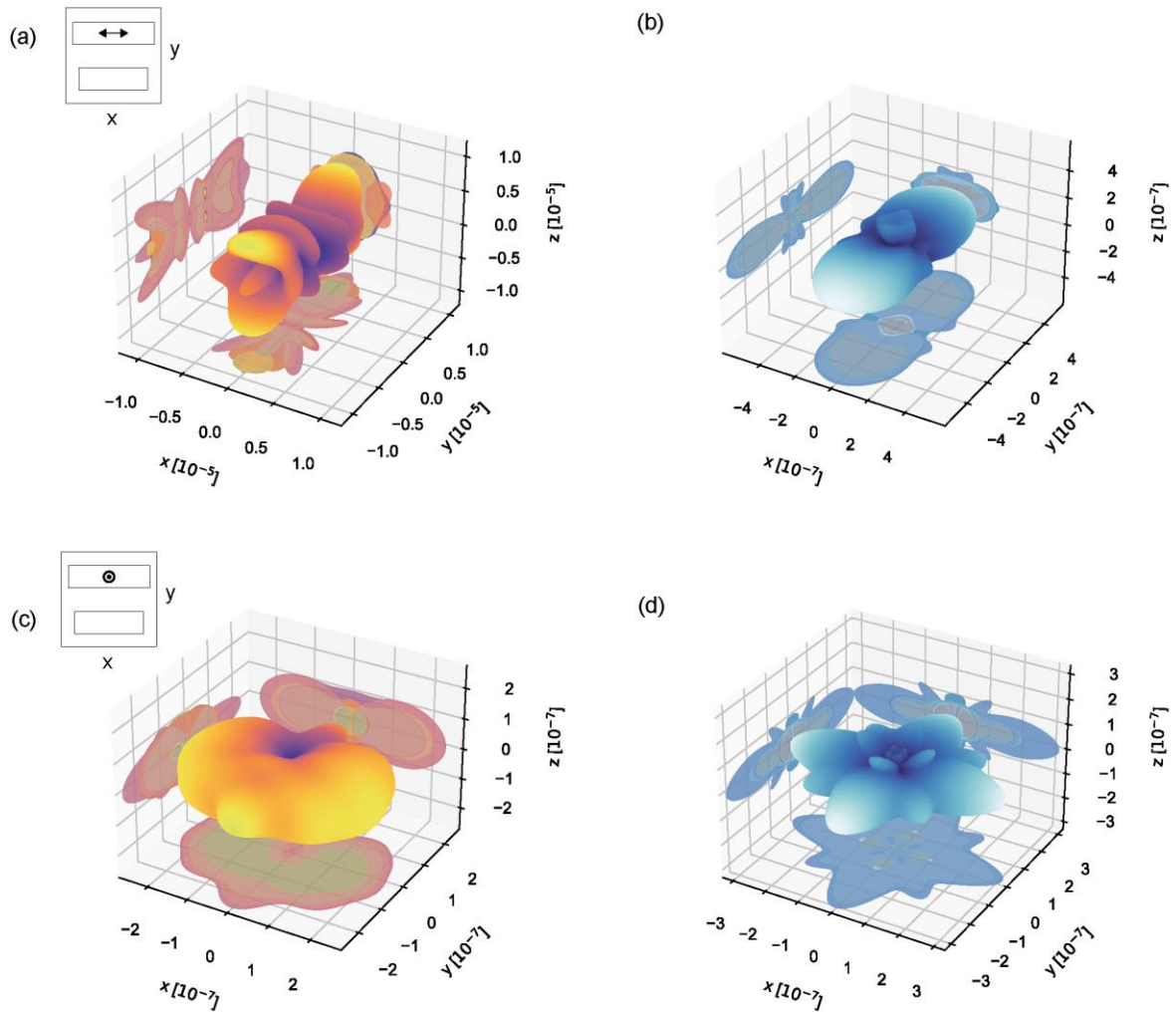


60 Supplementary Figure 5: (a-b) Profiles for the x (a) and y (b) electric field component, acquired at the
 61 qBIC resonance of an hBN metasurface, on SiO₂ substrates, with height of 160 nm and asymmetry of
 62 $\Delta L = 50$ nm. (c) Out-of-plane electric field intensity for the same unit cell.

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65 **Supplementary Note 6: Radiation patterns of in-plane and out-of-plane**
 66 **dipoles coupled with hBN metasurfaces.**



67 Supplementary Figure 6: (a-b) Numerical simulations of the far field patterns of the radiated electric
 68 field (E) for an in-plane dipole, aligned to the x-axis, coupled to the qBIC resonance (a) and in an hBN
 69 slab (b) of the same thickness. Inset: Position of the dipole considered for the numerical simulations,
 70 placed at the centre of the top nanorod, and with z position at half of the resonator height. (c-d)
 71 Numerically simulated far field patterns for an out-of-plane dipole emitter. For all the panels, the electric
 72 field component is projected along the relative axis.